Digital Transistors (BRT) R1 = 47 kΩ, R2 = ∞ kΩ

NPN Transistors with Monolithic Bias Resistor Network

MUN2240, MMUN2240L, MUN5240, DTC144TE, DTC144TM3, NSBC144TF3

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base–emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

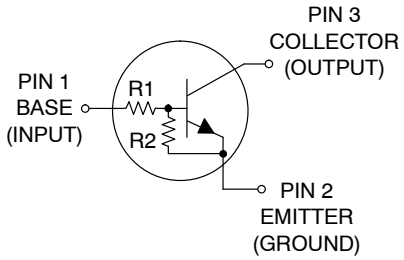
- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25 °C)

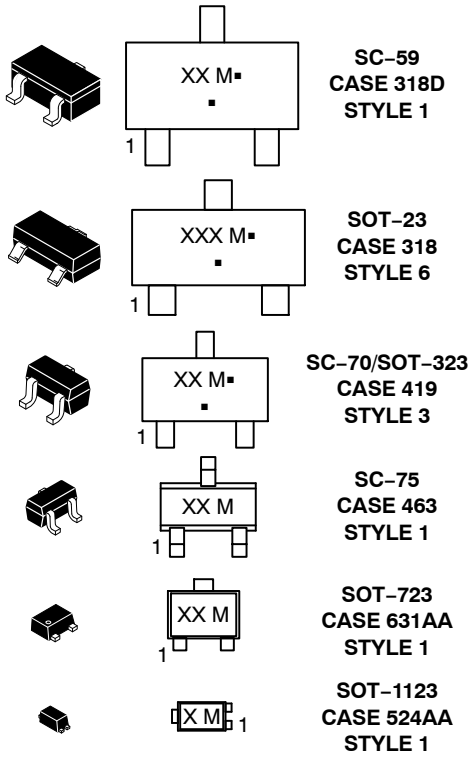
Rating	Symbol	Max	Unit
Collector–Base Voltage	V_{CBO}	50	Vdc
Collector–Emitter Voltage	V_{CEO}	50	Vdc
Collector Current – Continuous	I_C	100	mAdc
Input Forward Voltage	$V_{IN(fwd)}$	40	Vdc
Input Reverse Voltage	$V_{IN(rev)}$	6	Vdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

PIN CONNECTIONS



MARKING DIAGRAMS



XXX = Specific Device Code
M = Date Code*
▪ = Pb–Free Package

(Note: Microdot may be in either location)

* Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering, marking, and shipping information on page 2 of this data sheet.

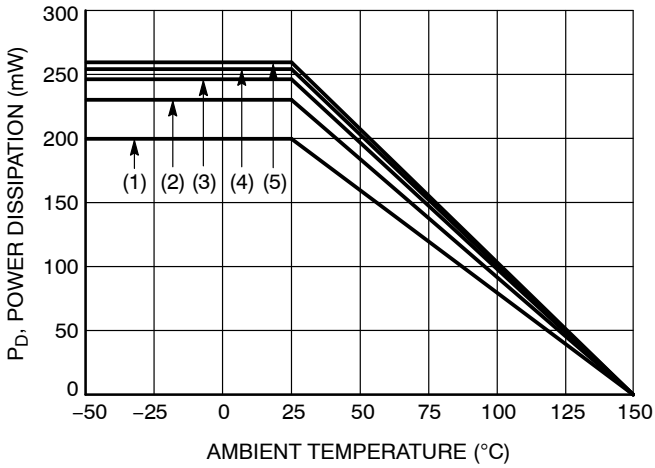
© Semiconductor Components Industries, LLC, 2012

Table 1. ORDERING INFORMATION

Device	Part Marking	Package	Shipping†
MUN2240T1G, SMUN2240T1G	8T	SC−59 (Pb−Free)	3000 / Tape & Reel
MMUN2240LT1G	AA4	SOT−23 (Pb−Free)	3000 / Tape & Reel
MUN5240T1G	AR	SC−70/SOT−323 (Pb−Free)	3000 / Tape & Reel
DTC144TET1G	7T	SC−75 (Pb−Free)	3000 / Tape & Reel
DTC144TM3T5G, NSVDTC144TM3T5G	8T	SOT−723 (Pb−Free)	8000 / Tape & Reel
NSBC144TF3T5G	K (180°)	SOT−1123 (Pb−Free)	8000 / Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

* (xx°) = Degree rotation in the clockwise direction.



(1) SC−75 and SC−70/SOT323; Minimum Pad
(2) SC−59; Minimum Pad
(3) SOT−23; Minimum Pad
(4) SOT−1123; 100 mm^2, 1 oz. copper trace
(5) SOT−723; Minimum Pad

Figure 1. Derating Curve

Share Feedback
Your Opinion Matters

Table 2. THERMAL CHARACTERISTICS

Characteristic		Symbol	Max	Unit
THERMAL CHARACTERISTICS (SC−59) (MUN2240)				
Total Device Dissipation T_A = 25 °C Derate above 25 °C	 (Note 1) (Note 2) (Note 1) (Note 2)	P_D	 230 338 1.8 2.7	 mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{\theta JA}$	540 370	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{\theta JL}$	264 287	°C/W
Junction and Storage Temperature Range		T_J, T_{stg}	−55 to +150	°C
THERMAL CHARACTERISTICS (SOT−23) (MMUN2240L)				
Total Device Dissipation T_A = 25 °C Derate above 25 °C	 (Note 1) (Note 2) (Note 1) (Note 2)	P_D	 246 400 2.0 3.2	 mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{\theta JA}$	508 311	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{\theta JL}$	174 208	°C/W
Junction and Storage Temperature Range		T_J, T_{stg}	−55 to +150	°C
THERMAL CHARACTERISTICS (SC−70/SOT−323) (MUN5240)				
Total Device Dissipation T_A = 25 °C Derate above 25 °C	 (Note 1) (Note 2) (Note 1) (Note 2)	P_D	 202 310 1.6 2.5	 mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{\theta JA}$	618 403	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{\theta JL}$	280 332	°C/W
Junction and Storage Temperature Range		T_J, T_{stg}	−55 to +150	°C
THERMAL CHARACTERISTICS (SC−75) (DTC144TE)				
Total Device Dissipation T_A = 25 °C Derate above 25 °C	 (Note 1) (Note 2) (Note 1) (Note 2)	P_D	 200 300 1.6 2.4	 mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{\theta JA}$	600 400	°C/W
Junction and Storage Temperature Range		T_J, T_{stg}	−55 to +150	°C
THERMAL CHARACTERISTICS (SOT−723) (DTC144TM3)				
Total Device Dissipation T_A = 25 °C Derate above 25 °C	 (Note 1) (Note 2) (Note 1) (Note 2)	P_D	 260 600 2.0 4.8	 mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{\theta JA}$	480 205	°C/W

1. FR−4 @ Minimum Pad.
2. FR−4 @ 1.0 x 1.0 Inch Pad.
3. FR−4 @ 100 mm^2, 1 oz. copper traces, still air.
4. FR−4 @ 500 mm^2, 1 oz. copper traces, still air.

Share Feedback
Your Opinion Matters

Table 2. THERMAL CHARACTERISTICS

Characteristic		Symbol	Max	Unit
THERMAL CHARACTERISTICS (SOT−723) (DTC144TM3)				
Junction and Storage Temperature Range		T_J, T_{stg}	−55 to +150	°C
THERMAL CHARACTERISTICS (SOT−1123) (NSBC144TF3)				
Total Device Dissipation T_A = 25 °C (Note 4) Derate above 25 °C (Note 4)	 (Note 3) (Note 3)	P_D	 254 297 2.0 2.4	 mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 3) (Note 4)	$R_{\theta JA}$	493 421	°C/W
Thermal Resistance, Junction to Lead	(Note 3)	$R_{\theta JL}$	193	°C/W
Junction and Storage Temperature Range		T_J, T_{stg}	−55 to +150	°C

1. FR−4 @ Minimum Pad.
2. FR−4 @ 1.0 x 1.0 Inch Pad.
3. FR−4 @ 100 mm^2, 1 oz. copper traces, still air.
4. FR−4 @ 500 mm^2, 1 oz. copper traces, still air.

Table 3. ELECTRICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector−Base Cutoff Current (V_{CB} = 50 V, I_E = 0)	I_{CBO}	–	–	100	nAdc
Collector−Emitter Cutoff Current (V_{CE} = 50 V, I_B = 0)	I_{CEO}	–	–	500	nAdc
Emitter−Base Cutoff Current (V_{EB} = 6.0 V, I_C = 0)	I_{EBO}	–	–	0.2	mAdc
Collector−Base Breakdown Voltage (I_C = 10 μA, I_E = 0)	$V_{(BR)CBO}$	50	–	–	Vdc
Collector−Emitter Breakdown Voltage (Note 5) (I_C = 2.0 mA, I_B = 0)	$V_{(BR)CEO}$	50	–	–	Vdc
ON CHARACTERISTICS					
DC Current Gain (Note 5) (I_C = 5.0 mA, V_{CE} = 10 V)	h_{FE}	120	300	–	
Collector−Emitter Saturation Voltage (Note 5) (I_C = 10 mA, I_B = 1.0 mA)	$V_{CE(sat)}$	–	–	0.25	Vdc
Input Voltage (off) (V_{CE} = 5.0 V, I_C = 100 μA)	$V_{i(off)}$	–	0.6	0.5	Vdc
Input Voltage (on) (V_{CE} = 0.3 V, I_C = 10 mA)	$V_{i(on)}$	4.0	2.6	–	Vdc
Output Voltage (on) (V_{CC} = 5.0 V, V_B = 3.5 V, R_L = 1.0 kΩ)	V_{OL}	–	–	0.2	Vdc
Output Voltage (off) (V_{CC} = 5.0 V, V_B = 0.25 V, R_L = 1.0 kΩ)	V_{OH}	4.9	–	–	Vdc
Input Resistor	R1	32.9	47	61.1	kΩ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulsed Condition: Pulse Width = 300 ms, Duty Cycle ≤ 2%.

Share Feedback
Your Opinion Matters

TYPICAL CHARACTERISTICS – MUN2240, MMUN2240L, MUN5240, DTC144TE, DTC144TM3

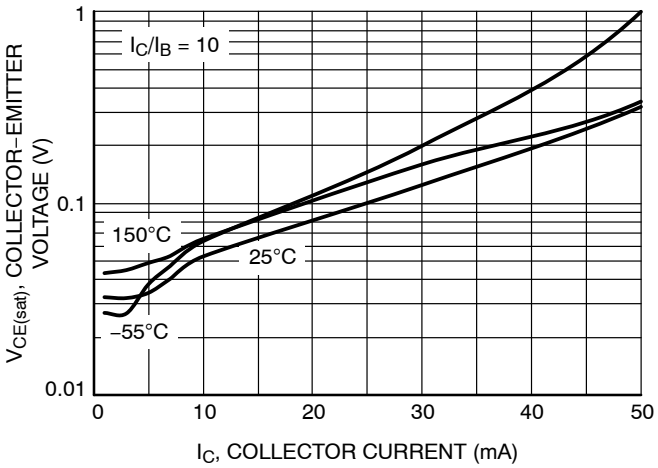


Figure 2. $V_{CE(sat)}$ vs. I_C

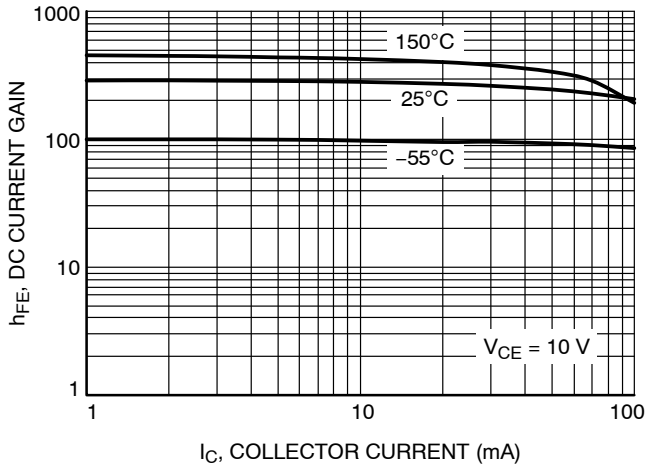


Figure 3. DC Current Gain

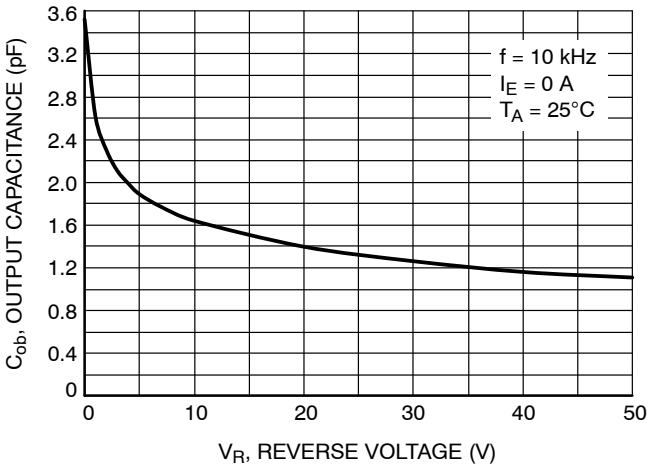


Figure 4. Output Capacitance

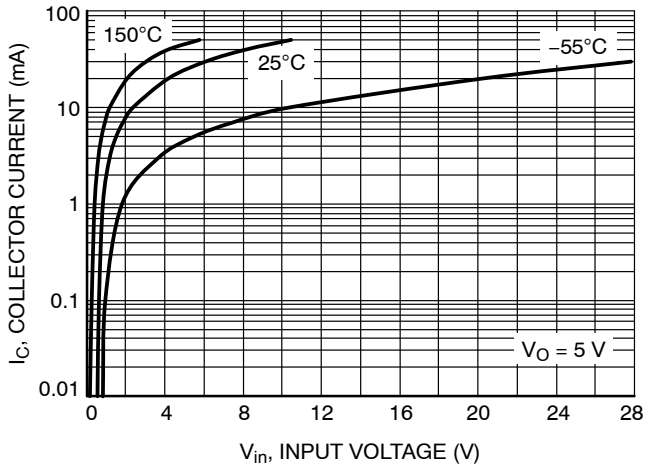


Figure 5. Output Current vs. Input Voltage

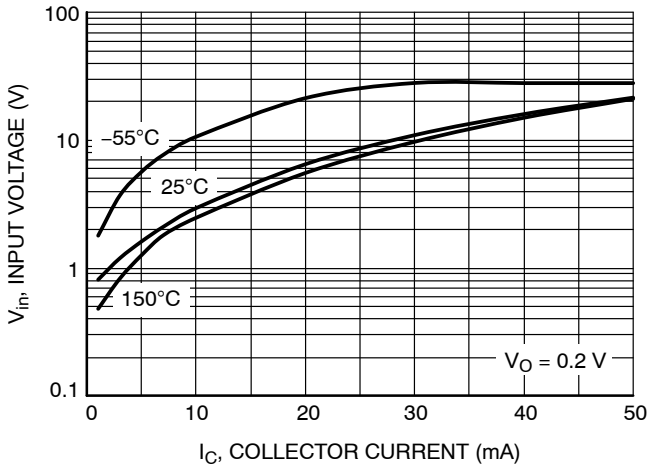


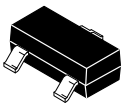
Figure 6. Input Voltage vs. Output Current

Share Feedback
Your Opinion Matters

REVISION HISTORY

Revision	Description of Changes	Date
5	Rebranded the Data Sheet to **onsemi** format.	06/19/2025

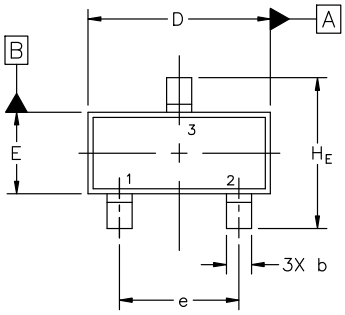
Share Feedback
Your Opinion Matters



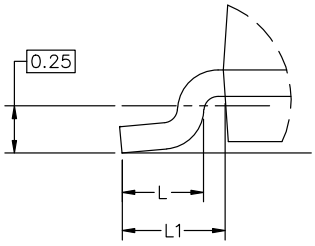
SCALE 4:1

SOT−23 (TO−236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

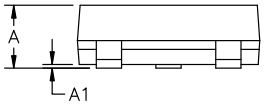
DATE 14 AUG 2024



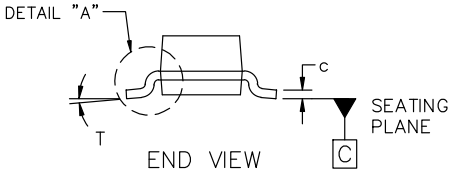
TOP VIEW



DETAIL "A"
Scale 3:1



SIDE VIEW

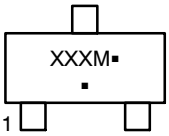


END VIEW

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.89	1.00	1.11
A1	0.01	0.06	0.10
b	0.37	0.44	0.50
c	0.08	0.14	0.20
D	2.80	2.90	3.04
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.43	0.55
L1	0.35	0.54	0.69
H_E	2.10	2.40	2.64
T	0°	−−−	10°

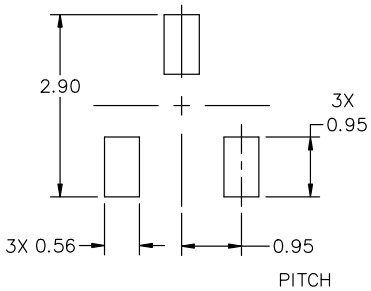
NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED
MOUNTING FOOTPRINT

* For additional information on our Pb−Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

DOCUMENT NUMBER:	**98ASB42226B**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	**SOT−23 (TO−236) 2.90x1.30x1.00 1.90P**	**PAGE 1 OF 2**

onsemi and onsemi are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

SOT−23 (TO−236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE−ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE−ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

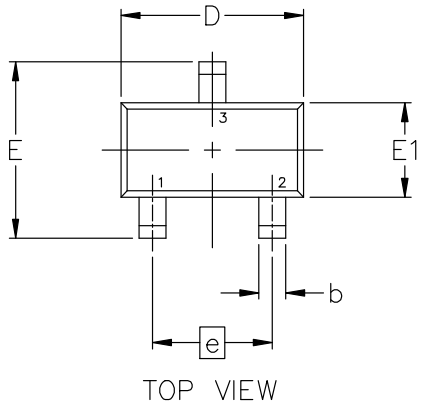
STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

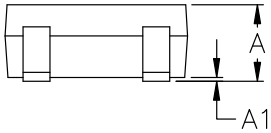
onsemi and onsemi are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

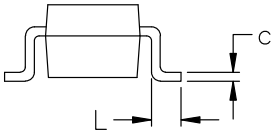
© Semiconductor Components Industries, LLC, 2019

SC−59−3 2.90x1.50x1.15, 1.90P
CASE 318D
ISSUE J

DATE 15 FEB 2024



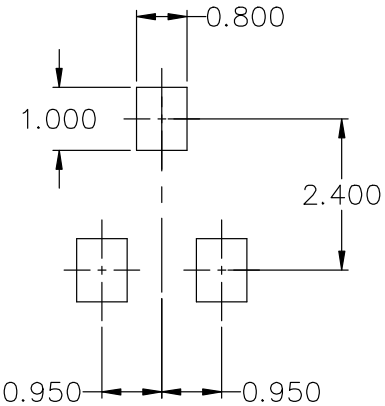




NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5−2018.
2. ALL DIMENSION ARE IN MILLIMETERS.

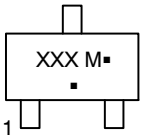
DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	1.00	1.15	1.30
A1	0.01	0.06	0.10
b	0.35	0.43	0.50
c	0.09	0.14	0.18
D	2.70	2.90	3.10
E	2.50	2.80	3.00
E1	1.30	1.50	1.70
e	1.90 BSC		
L	0.20	0.40	0.60



RECOMMENDED MOUNTING FOOTPRINT*

* FOR ADDITIONAL INFORMATION ON OUR Pb−FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package*

(*Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 2:
PIN 1. ANODE
2. N.C.
3. CATHODE

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

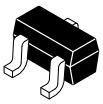
STYLE 4:
PIN 1. CATHODE
2. N.C.
3. ANODE

STYLE 5:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE/CATHODE

DOCUMENT NUMBER:	98ASB42664B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.
DESCRIPTION:	SC−59−3 2.90x1.50x1.15, 1.90P	PAGE 1 OF 1

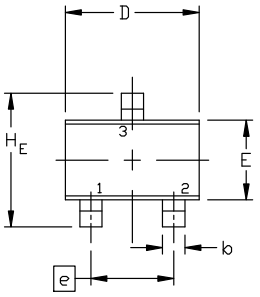
onsemi and onsemi are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.



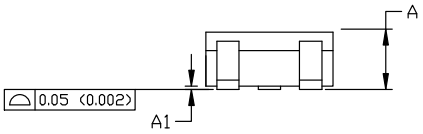
SCALE 4:1

SC−70 (SOT−323)
CASE 419
ISSUE R

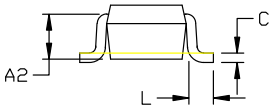
DATE 11 OCT 2022



TOP VIEW



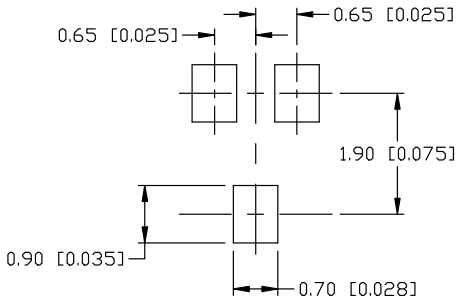
SIDE VIEW



END VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH

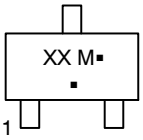
DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
H_E	2.00	2.10	2.40	0.079	0.083	0.095



* For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

SOLDERING FOOTPRINT

GENERIC MARKING DIAGRAM



XX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
CANCELLED

STYLE 2:
PIN 1. ANODE
2. N.C.
3. CATHODE

STYLE 3:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 6:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 7:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 8:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 9:
PIN 1. ANODE
2. CATHODE
3. CATHODE−ANODE

STYLE 10:
PIN 1. CATHODE
2. ANODE
3. ANODE−CATHODE

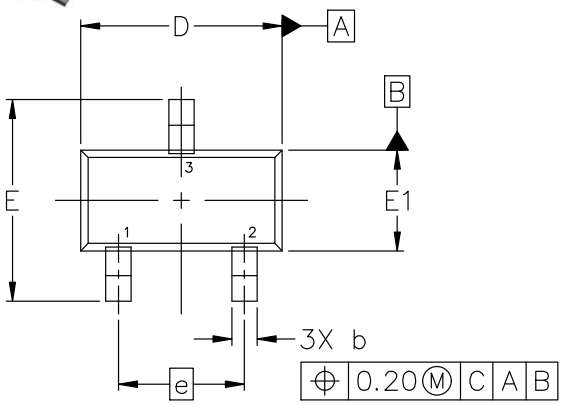
STYLE 11:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

DOCUMENT NUMBER:	98ASB42819B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.	
DESCRIPTION:	SC−70 (SOT−323)		PAGE 1 OF 1

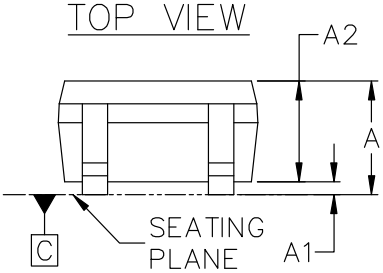
onsemi and onsemi are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

SC75−3 1.60x0.80x0.80, 1.00P
CASE 463
ISSUE H

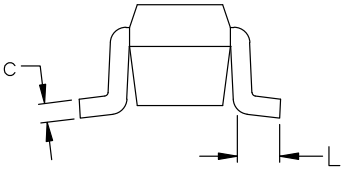
DATE 01 FEB 2024



TOP VIEW



SIDE VIEW



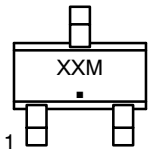
END VIEW

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5−2018.
2. ALL DIMENSION ARE IN MILLIMETERS.

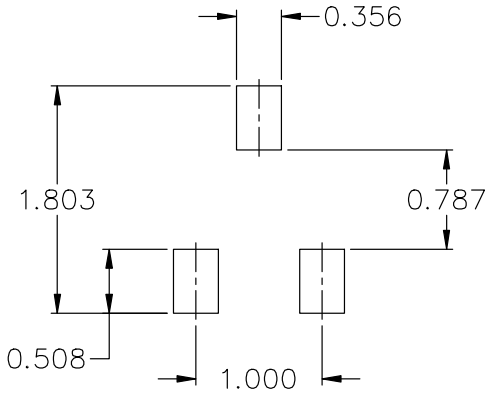
DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.70	0.80	0.90
A1	0.00	0.05	0.10
A2	0.80 REF.		
b	0.15	0.20	0.30
c	0.10	0.15	0.25
D	1.55	1.60	1.65
E	1.50	1.60	1.70
E1	0.70	0.80	0.90
e	1.00 BSC		
L	0.10	0.15	0.20

GENERIC MARKING DIAGRAM*



XX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT*

* FOR ADDITIONAL INFORMATION ON OUR Pb−FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 2:
PIN 1. ANODE
2. N/C
3. CATHODE

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

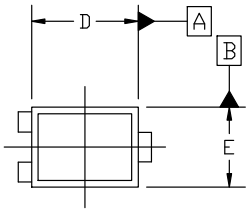
STYLE 5:
PIN 1. GATE
2. SOURCE
3. DRAIN

DOCUMENT NUMBER:	98ASB15184C	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.
DESCRIPTION:	SC75−3 1.60x0.80x0.80, 1.00P	PAGE 1 OF 1

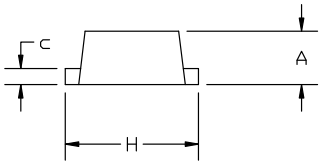
onsemi and onsemi are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

SOT−1123 0.80x0.60x0.37, 0.35P
CASE 524AA
ISSUE D

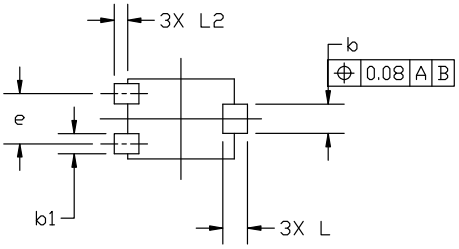
DATE 18 JAN 2024



TOP VIEW



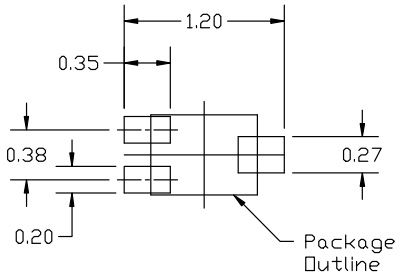
SIDE VIEW



BOTTOM VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.34	0.37	0.40
b	0.15	0.22	0.28
b1	0.10	0.15	0.20
c	0.07	0.12	0.17
D	0.75	0.80	0.85
E	0.55	0.60	0.65
e	0.35	0.38	0.40
H	0.950	1.000	1.050
L	0.185 REF		
L2	0.05	0.10	0.15



RECOMMENDED
MOUNTING FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download th e ON Semiconductor Soldering and Mounting Techniques Reference manual, SOLDERRM/D.

**GENERIC
MARKING DIAGRAM***

X = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 2:
PIN 1. ANODE
2. N/C
3. CATHODE

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. GATE
2. SOURCE
3. DRAIN

DOCUMENT NUMBER:	98AON23134D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.
DESCRIPTION:	SOT−1123 0.80x0.60x0.37, 0.35P	PAGE 1 OF 1

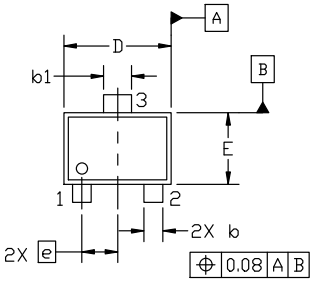
onsemi and onsemi are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

SOT−723 1.20x0.80x0.50, 0.40P
CASE 631AA
ISSUE E

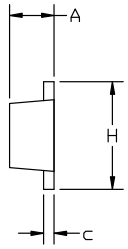
DATE 24 JAN 2024

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

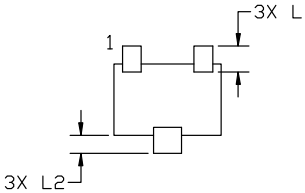
DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
c	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
e	0.40 BSC		
H	1.15	1.20	1.25
L	0.29 REF		
L2	0.15	0.20	0.25



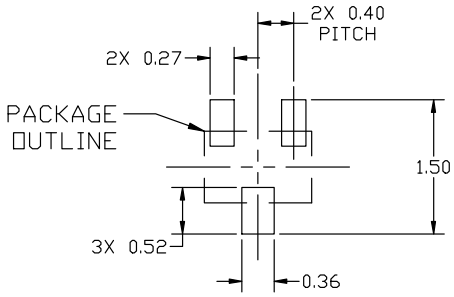
TOP VIEW



SIDE VIEW



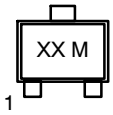
BOTTOM VIEW



RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XX = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 2:
PIN 1. ANODE
2. N/C
3. CATHODE

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. GATE
2. SOURCE
3. DRAIN

DOCUMENT NUMBER:	98AON12989D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.
DESCRIPTION:	SOT−723 1.20x0.80x0.50, 0.40P	PAGE 1 OF 1

onsemi and onsemi are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

onsemi, onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent−Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as−is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at
www.onsemi.com/support/sales